

FDS6609A

P-Channel Logic Level PowerTrench® MOSFET

General Description

This P-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

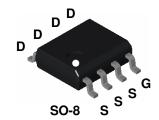
These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

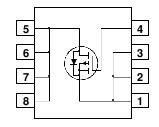
Applications

- DC/DC converter
- · Load switch
- Motor Drive

Features

- $-6.3 \text{ A}, -30 \text{ V}. \text{ R}_{DS(ON)} = 0.032 \Omega \text{ @ V}_{GS} = -10 \text{ V}$ $\text{R}_{DS(ON)} = 0.05 \Omega \text{ @ V}_{GS} = -4.5 \text{ V}$
- · Low gate charge
- · Fast switching speed
- High performance trench technology for extremely low R_{DS(ON)}
- High power and current handling capability





Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		±20	V
l _D	Drain Current - Continuous	(Note 1a)	-6.3	A
	- Pulsed		-40	
P _D	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1.0	
T_J , T_{STG}	Operating and Storage Junction Temperat	ture Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
ReJC	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W

Package Marking and Ordering Information

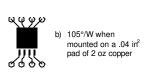
Device Marking	Device	Reel Size	Tape width	Quantity	
FDS6609A	FDS6609A	13"	12mm	2500 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics			I		ı
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-30			V
<u>ΔBV DSS</u> ΔTJ	Breakdown Voltage Temperature Coefficient	I_D = -250 μA, Referenced to 25°C		-22		mV/°C
loss	Zero Gate Voltage Drain Current	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
Igssf	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)			•		•
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{CS}, I_D = -250 \mu A$	-1	-1.5	-3	V
ΔVGS(th) ΔTJ	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to 25°C		4		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	$\begin{split} V_{GS} &= -10 \text{ V}, & I_D = -7.0 \text{ A} \\ V_{GS} &= -4.5 \text{ V}, & I_D = -5.5 \text{ A} \\ V_{GS} &= -10 \text{ V}, I_D = -7.0 \text{A}, T_J = 125 ^{\circ}\text{C} \end{split}$		0.027 0.04 0.04	0.032 0.05 0.54	Ω
I _{D(on)}	On-State Drain Current	$V_{GS} = -10 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	-20			Α
g fs	Forward Transconductance	$V_{DS} = -10 \text{ V}, \qquad I_D = -7.0 \text{ A}$		14.5		S
Dvnamio	Characteristics					
Ciss	Input Capacitance	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V},$		930		pF
Coss	Output Capacitance	f = 1.0 MHz		278		pF
C _{rss}	Reverse Transfer Capacitance	1		114		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -15 V$, $I_D = -1 A$,		12	21	ns
tr	Turn-On Rise Time	$V_{GS} = -10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		11	20	ns
t _{d(off)}	Turn-Off Delay Time	1		33	52	ns
t _f	Turn-Off Fall Time	1		13	23	ns
Qg	Total Gate Charge	$V_{DS} = -15 \text{ V}, I_{D} = -7.2 \text{ A},$		18	29	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -10 \text{ V}$		2.5		nC
Q_{gd}	Gate-Drain Charge	1		4.1		nC
Drain-Se	ource Diode Characteristics	and Maximum Ratings				
ls	Maximum Continuous Drain-Source				-2.1	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -2.1 \text{ A} \text{(Note 2)}$		-0.76	-1.2	V

1. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50°/W when mounted on a 1in² pad of 2 oz copper





c) 125°/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width < $300\mu s$, Duty Cycle < 2.0%

Typical Characteristics

 $I_D = -7A$

= -10V

R_{DS(ON)} NORMALIZED DRAIN-SOURCE ON-RESISTANCE

1.4

1.2

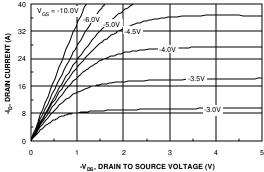


Figure 1. On-Region Characteristics.



Figure 3. On-Resistance Variation with Temperature.

 $T_{_{\mathcal{I}}}$ JUNCTION TEMPERATURE (°C)

75

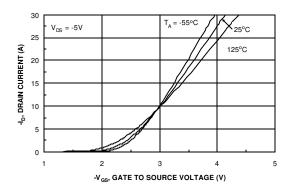


Figure 5. Transfer Characteristics.

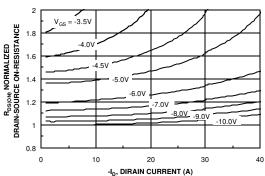


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

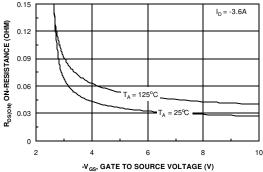


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

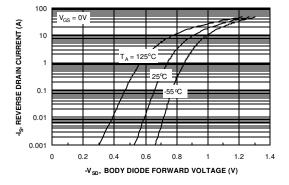
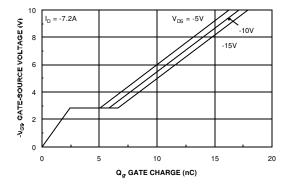


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



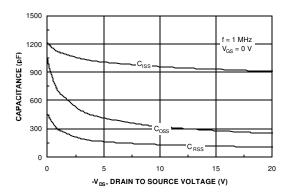
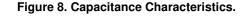
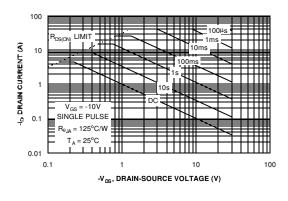


Figure 7. Gate Charge Characteristics.





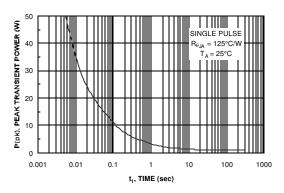


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

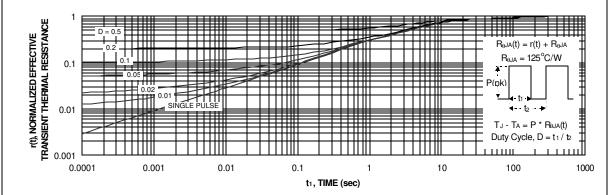
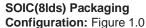


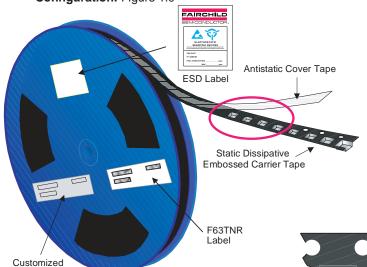
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

SO-8 Tape and Reel Data and Package Dimensions





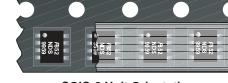


Packaging Description:

Packaging Description:

SOIC-8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and amit-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13° or 300cm diameter reel. The releas are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 500 units per 7° or 177cm diameter reel. This and some other options are further described in the Packaging Information table.

These full reles are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.





SOIC-8 Unit Orientation

SOIC (8lds) Packaging Information Packaging Option Standard o flow code) L86Z D84Z Rail/Tube TNR Packaging type TNR TNR Qty per Reel/Tube/Bag 2.500 4.000 500 Reel Size 13" Dia 13" Dia 7" Dia Box Dimension (mm) 343y64y343 530x130x83 343y64y343 184v187v47 Max qty per Box 5,000 30,000 8,000 1,000 Weight per unit (gm) 0.0774 0.0774 0.0774 0.0774 Weight per Reel (kg) 0.6060 0.9696 0.1182 Note/Comments

F63TNR Label sample

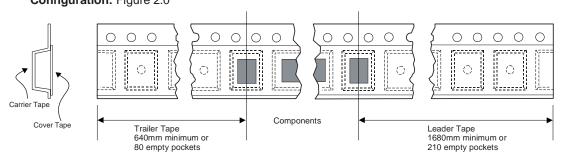
Label



F63TNLabel F63TN Label

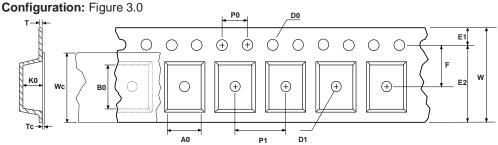
343mm x 342mm x 64mm

SOIC(8lds) Tape Leader and Trailer Configuration: Figure 2.0





SOIC(8lds) Embossed Carrier Tape



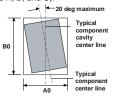


	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOIC(8lds) (12mm)	6.50 +/-0.10	5.30 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	2.1 +/-0.10	0.450 +/- 0.150	9.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)

Component Rotation

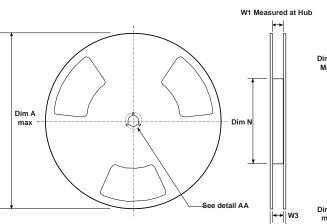


Sketch C (Top View)

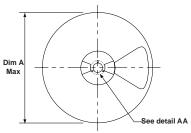
Component lateral movement

SOIC(8lds) Reel Configuration: Figure 4.0

Tape Size



13" Diameter Option W2 max Measured at Hub



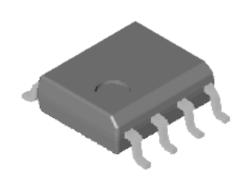
7" Diameter Option Dim C Dim D

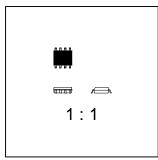
DETAIL AA

Dimensions are in inches and millimeters								
Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
7" Dia	7.00	0.059	512 +0.020/-0.008	0.795	2.165	0.488 +0.078/-0.000	0.724	0.469 - 0.606
	177.8	1.5	13 +0.5/-0.2	20.2	55	12.4 +2/0	18.4	11.9 - 15.4
13" Dia	13.00	0.059	512 +0.020/-0.008	0.795	7.00	0.488 +0.078/-0.000	0.724	0.469 - 0.606
	330	1.5	13 +0.5/-0.2	20.2	178	12.4 +2/0	18.4	11.9 - 15.4

SO-8 Tape and Reel Data and Package Dimensions, continued

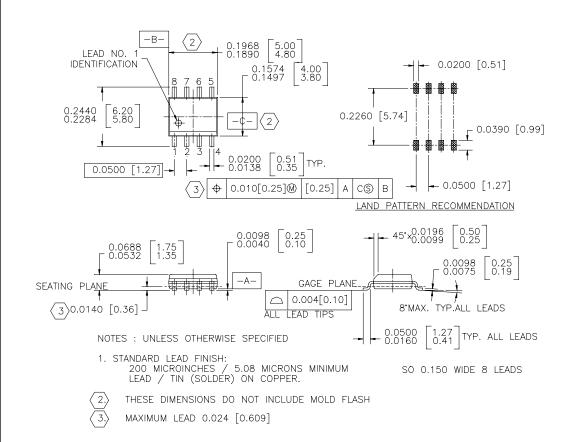
SOIC-8 (FS PKG Code S1)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0774



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PRODUCT STATUS DEFINITIONS

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Datasheet Identification	Product Status	Definition
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